

# CLEANING COMPOSITION AND METHOD OF WASHING A SILICON WAFER

## Abstract

The cleaning composition has a first acid for removing copper from the silicon wafer surface, an oxidizing agent for oxidizing the silicon wafer surface to form an oxide thin film and for oxidizing barrier residues on the bevel edges, a second acid for removing the oxide thin film, and deionized (DI) water. The method involves applying the cleaning composition to the silicon wafer surface for a process time, and spin-drying the silicon wafer surface. This removes all residues from the backside surface and the bevel edges of a silicon wafer.